



# STB57N65M5, STF57N65M5, STI57N65M5, STP57N65M5

N-channel 650 V, 0.056  $\Omega$  typ., 42 A MDmesh™ V Power MOSFET in I<sup>2</sup>PAK, TO-220, TO-220FP and D<sup>2</sup>PAK packages

Datasheet — production data

## Features

Order codes	V <sub>DSS</sub> @ T <sub>Jmax</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STB57N65M5 STF57N65M5 STI57N65M5 STP57N65M5	710 V	< 0.063 $\Omega$	42 A

- Worldwide best R<sub>DS(on)</sub>\*area amongst the silicon based devices
- Higher V<sub>DSS</sub> rating, high dv/dt capability
- Excellent switching performance
- Easy to drive, 100% avalanche tested

## Applications

- Switching applications

## Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

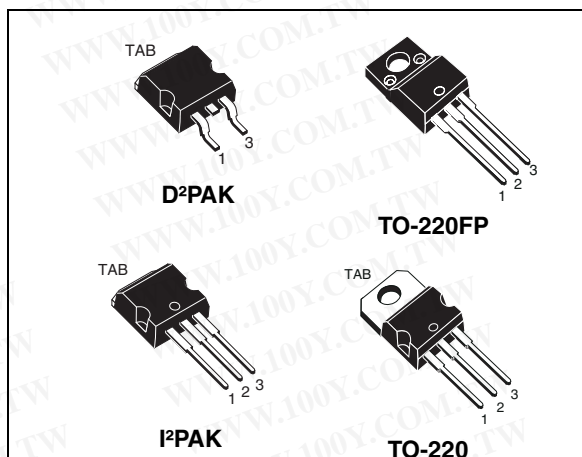


Figure 1. Internal schematic diagram

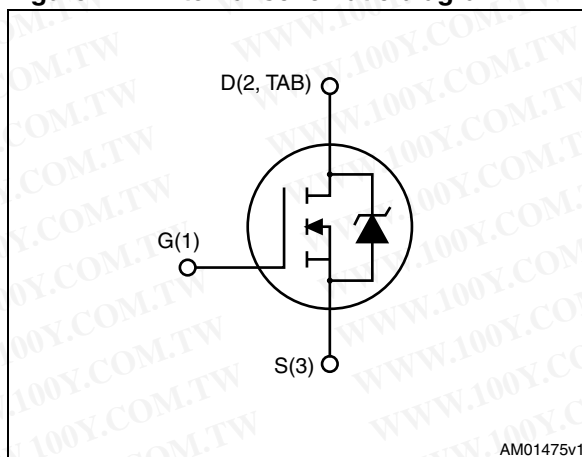


Table 1. Device summary

Order codes	Marking	Packages	Packaging
STB57N65M5 STF57N65M5 STI57N65M5 STP57N65M5	57N65M5	D <sup>2</sup> PAK TO-220FP I <sup>2</sup> PAK TO-220	Tape and reel Tube Tube Tube

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220, D <sup>2</sup> PAK, I <sup>2</sup> PAK	TO-220FP	
V <sub>GS</sub>	Gate- source voltage	± 25		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	42	42 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	26.5	26.5 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	168	168 <sup>(1)</sup>	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	250	40	W
I <sub>AR</sub>	Max current during repetitive or single pulse avalanche (pulse width limited by T <sub>JMAX</sub> )	11		A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>J</sub> = 25°C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50V)	960		mJ
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	15		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T <sub>C</sub> = 25 °C)	2500		V
T <sub>stg</sub>	Storage temperature	-55 to 150		°C
T <sub>j</sub>	Max. operating junction temperature	150		°C

1. Limited by maximum junction temperature.

2. Pulse width limited by safe operating area.

3. I<sub>SD</sub> ≤ 42 A, di/dt ≤ 400 A/μs, V<sub>Peak</sub> < V<sub>(BR)DSS</sub>, V<sub>DD</sub> = 400 V

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		D <sup>2</sup> PAK	I <sup>2</sup> PAK	TO-220	TO-220FP	
R <sub>thj-case</sub>	Thermal resistance junction-case max	0.50		3.1		°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	62.5		62.5		°C/W
R <sub>thj-pcb</sub>	Thermal resistance junction-pcb max <sup>(1)</sup>	30				°C/W

1. When mounted on 1inch<sup>2</sup> FR-4 board, 2 oz Cu.

## 2 Electrical characteristics

( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	650			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}$ , $T_C = 125\text{ }^\circ\text{C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 21\text{ A}$		0.056	0.063	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	4200	-	pF
$C_{oss}$	Output capacitance			115		
$C_{rss}$	Reverse transfer capacitance			9		
$C_{o(er)}^{(1)}$	Equivalent output capacitance energy related	$V_{GS} = 0$ , $V_{DS} = 0$ to 80% $V_{(BR)DSS}$	-	93	-	pF
$C_{o(tr)}^{(2)}$	Equivalent output capacitance time related	$V_{GS} = 0$ , $V_{DS} = 0$ to 80% $V_{(BR)DSS}$	-	303	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.3	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 21\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 18</a> )	-	98	-	nC
$Q_{gs}$	Gate-source charge			23		
$Q_{gd}$	Gate-drain charge			40		

1.  $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$

2.  $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(V)}$	Voltage delay time	$V_{DD} = 400\text{ V}$ , $I_D = 28\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 19</a> )	-	73	-	ns
$t_{r(V)}$	Voltage rise time		-	15	-	ns
$t_{f(i)}$	Current fall time		-	12	-	ns
$t_{c(off)}$	Crossing time		-	19	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		42	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		168	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 42\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 42\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see <a href="#">Figure 19</a> )	-	418		ns
$Q_{rr}$	Reverse recovery charge		-	8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	40		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 42\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 19</a> )	-	528		ns
$Q_{rr}$	Reverse recovery charge		-	12		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	44		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%



## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D<sup>2</sup>PAK, I<sup>2</sup>PAK and TO-220

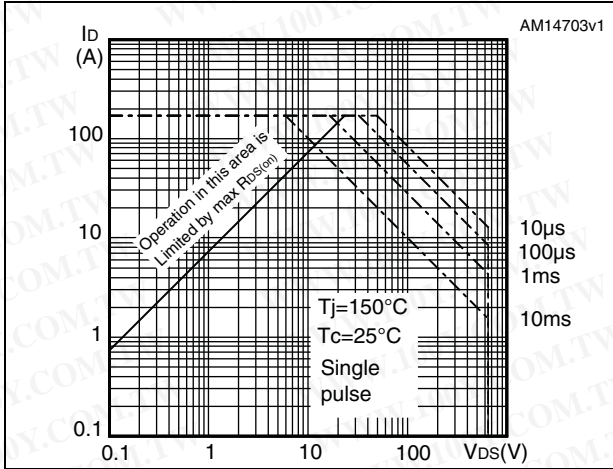


Figure 3. Thermal impedance for D<sup>2</sup>PAK, I<sup>2</sup>PAK and TO-220

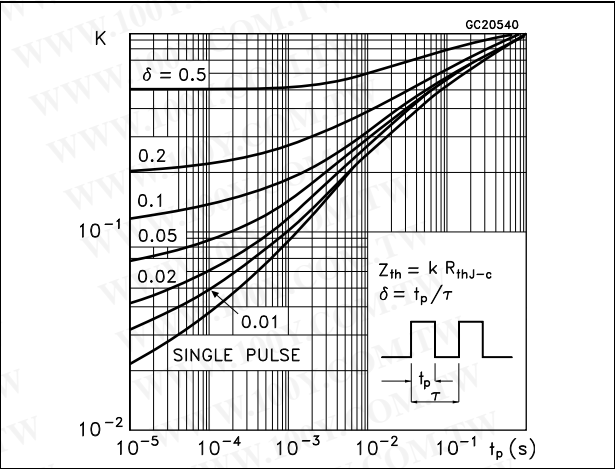


Figure 4. Safe operating area for TO-220FP

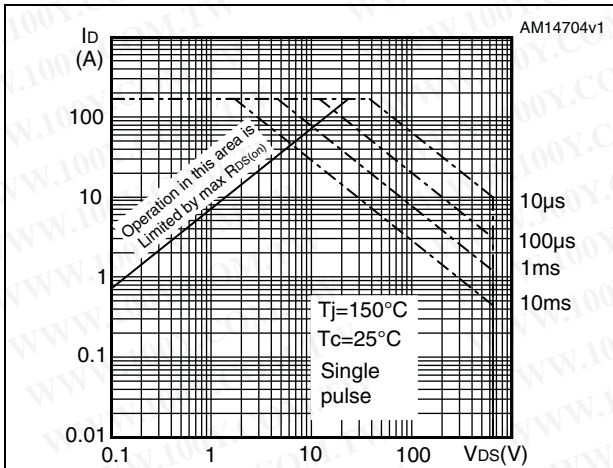


Figure 5. Thermal impedance for TO-220FP

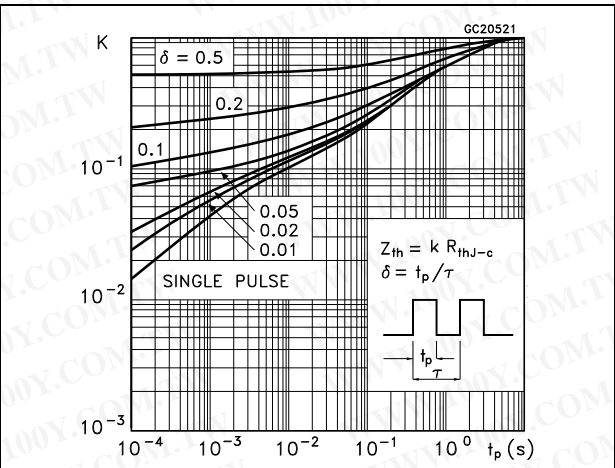


Figure 6. Output characteristics

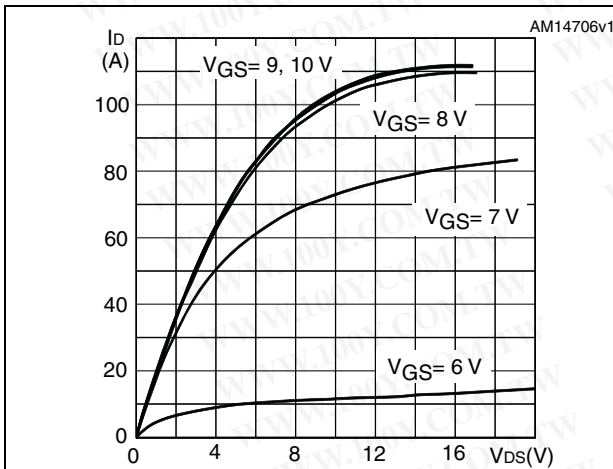


Figure 7. Transfer characteristics

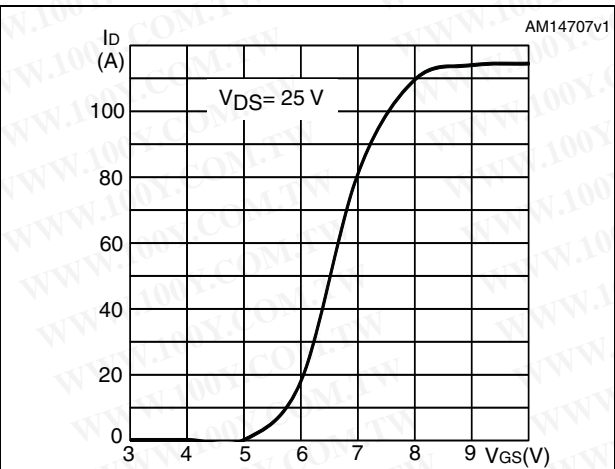


Figure 8. Gate charge vs gate-source voltage Figure 9. Static drain-source on-resistance

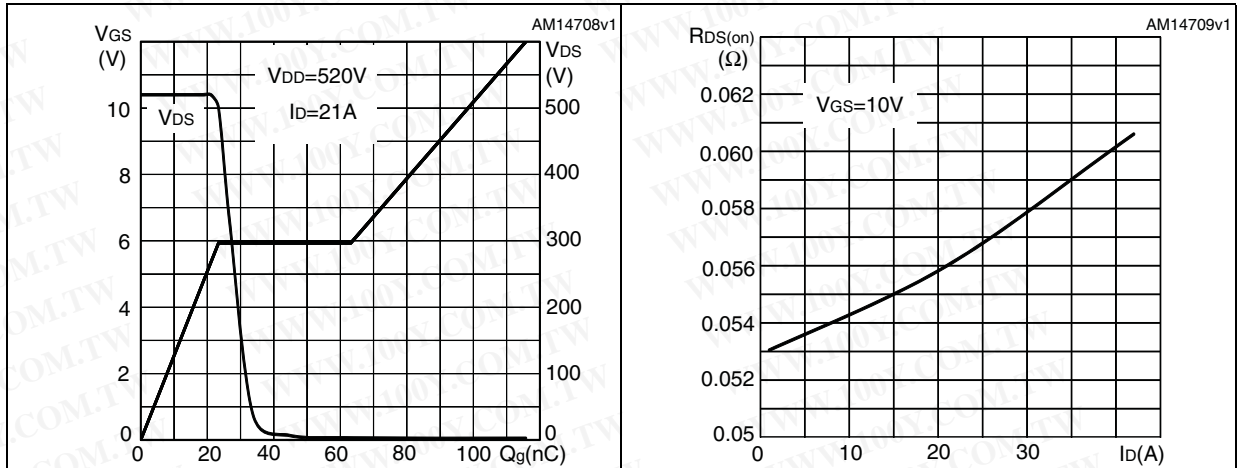


Figure 10. Capacitance variations Figure 11. Output capacitance stored energy

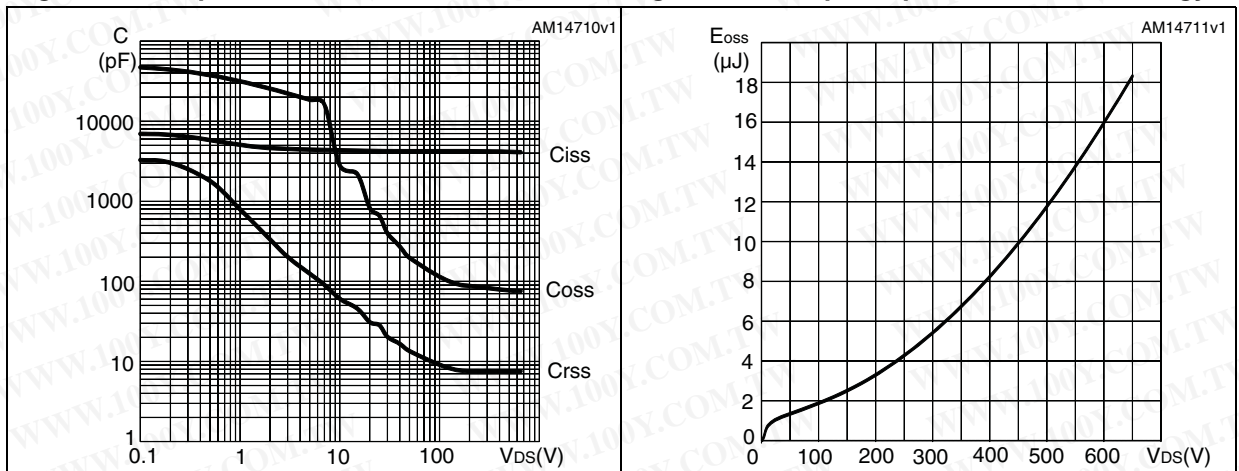


Figure 12. Normalized gate threshold voltage vs temperature Figure 13. Normalized on-resistance vs temperature

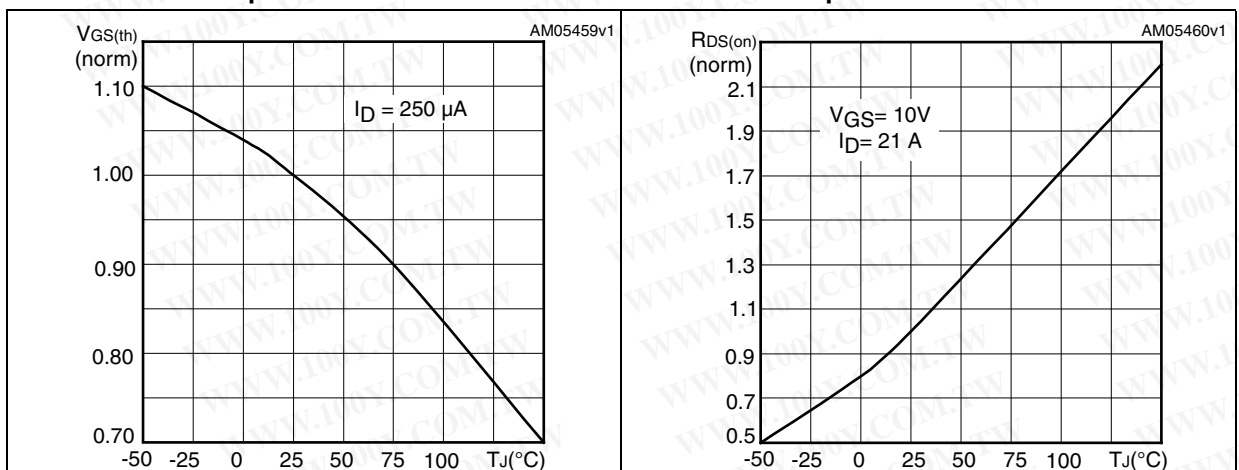


Figure 14. Source-drain diode forward characteristics

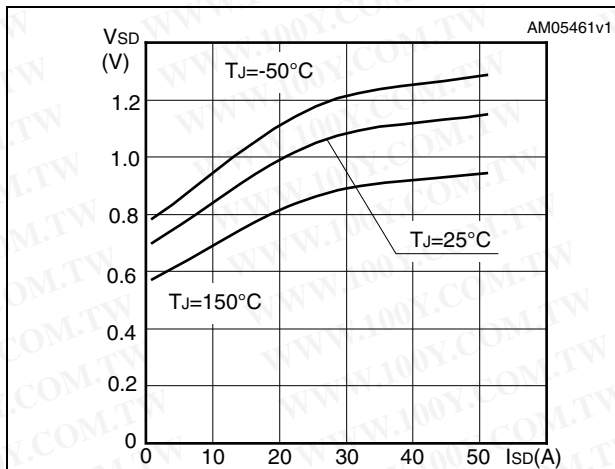


Figure 15. Normalized  $B_{VDSS}$  vs temperature

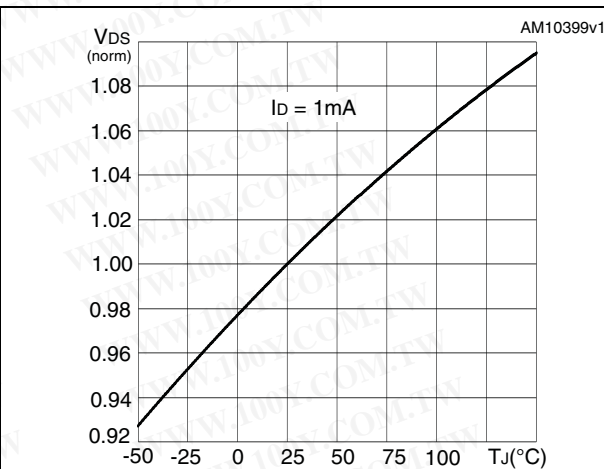
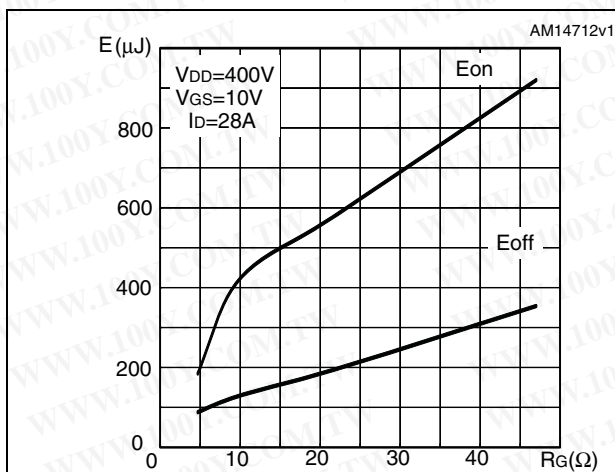


Figure 16. Switching losses vs gate resistance (1)



1. Eon including reverse recovery of a SiC diode



### 3 Test circuits

Figure 17. Switching times test circuit for resistive load

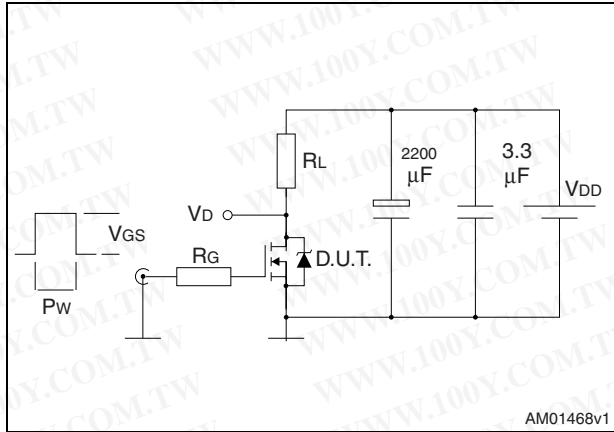


Figure 18. Gate charge test circuit

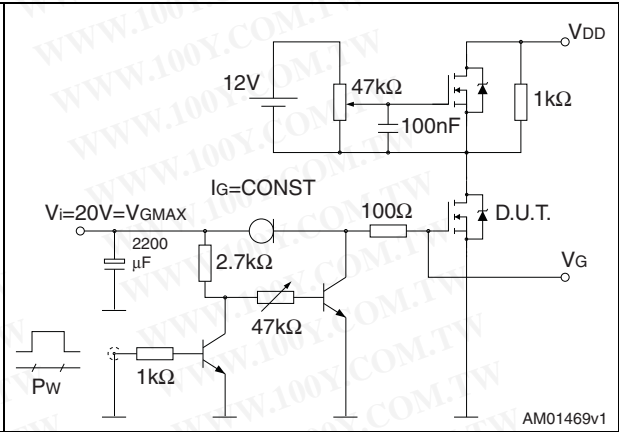


Figure 19. Test circuit for inductive load switching and diode recovery times

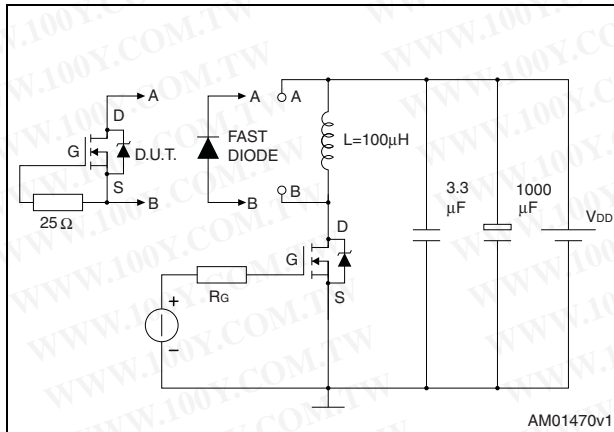


Figure 20. Unclamped inductive load test circuit

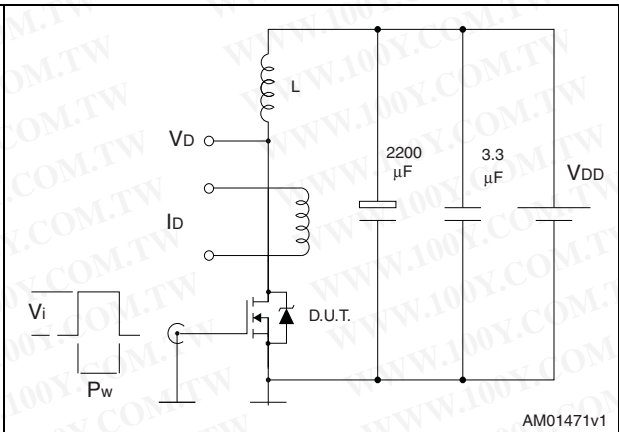


Figure 21. Unclamped inductive waveform

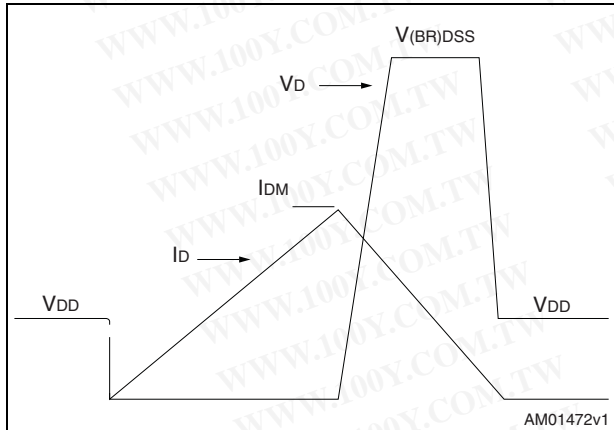
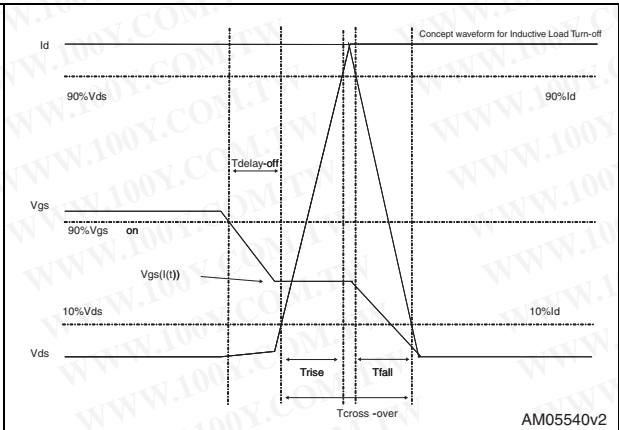


Figure 22. Switching time waveform



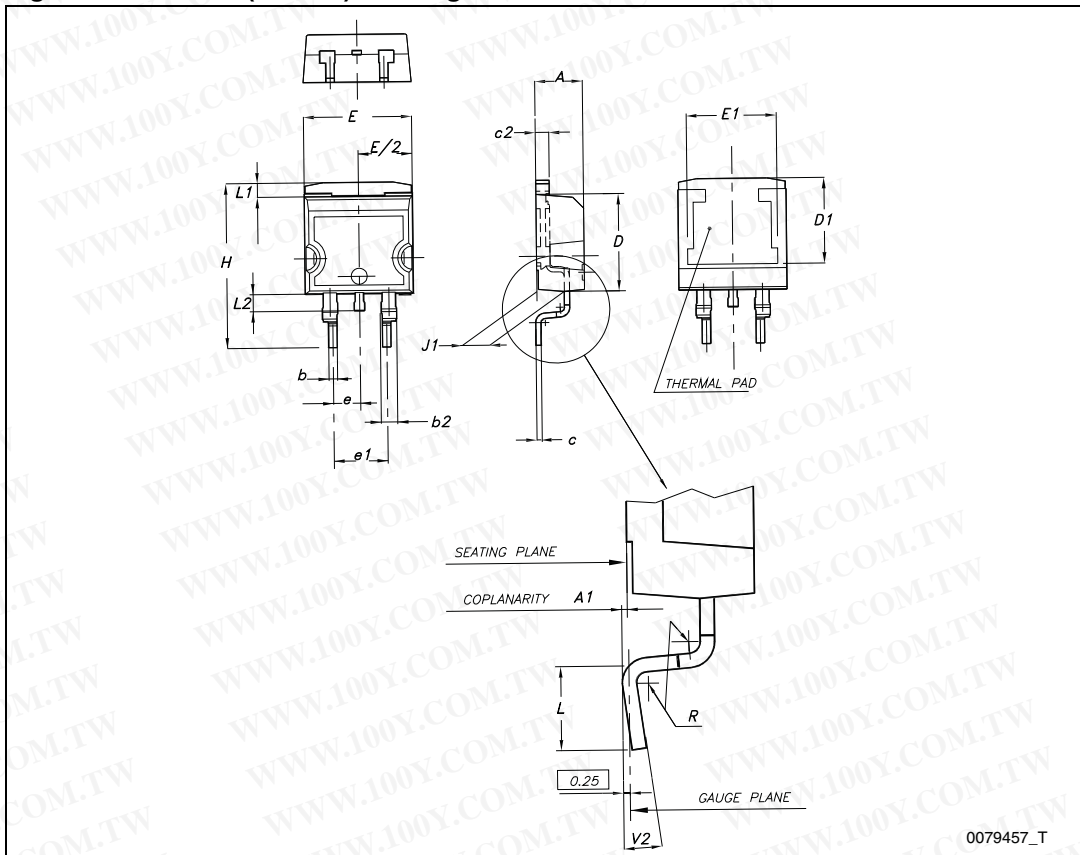
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 8. D<sup>2</sup>PAK (TO-263) mechanical data**

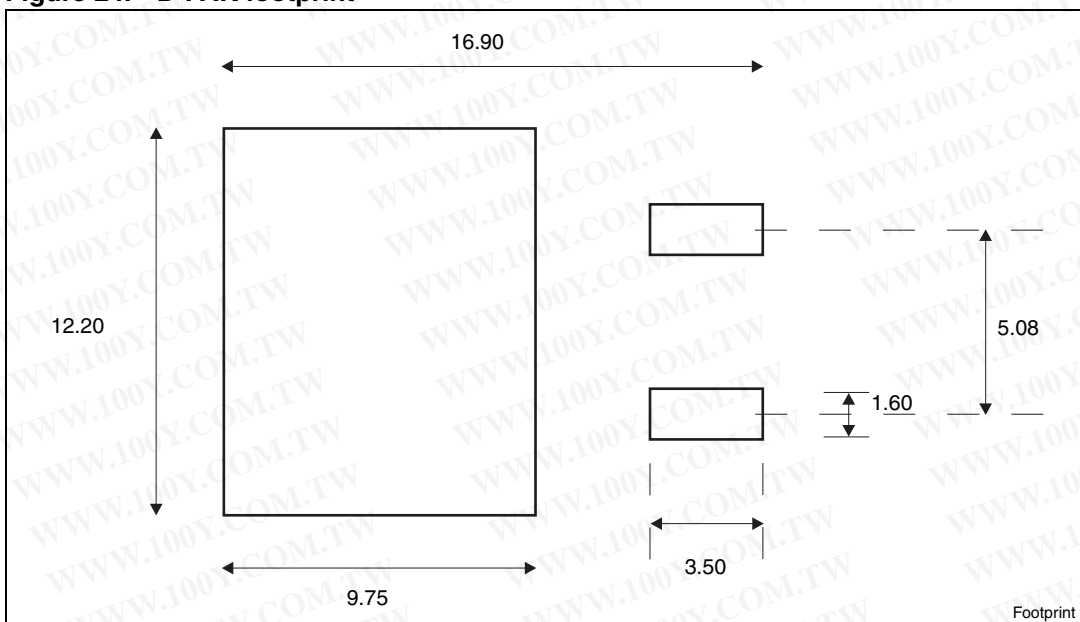
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 23. D<sup>2</sup>PAK (TO-263) drawing



0079457\_T

Figure 24. D<sup>2</sup>PAK footprint<sup>(a)</sup>



a. All dimension are in millimeters

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 25. TO-220FP drawing

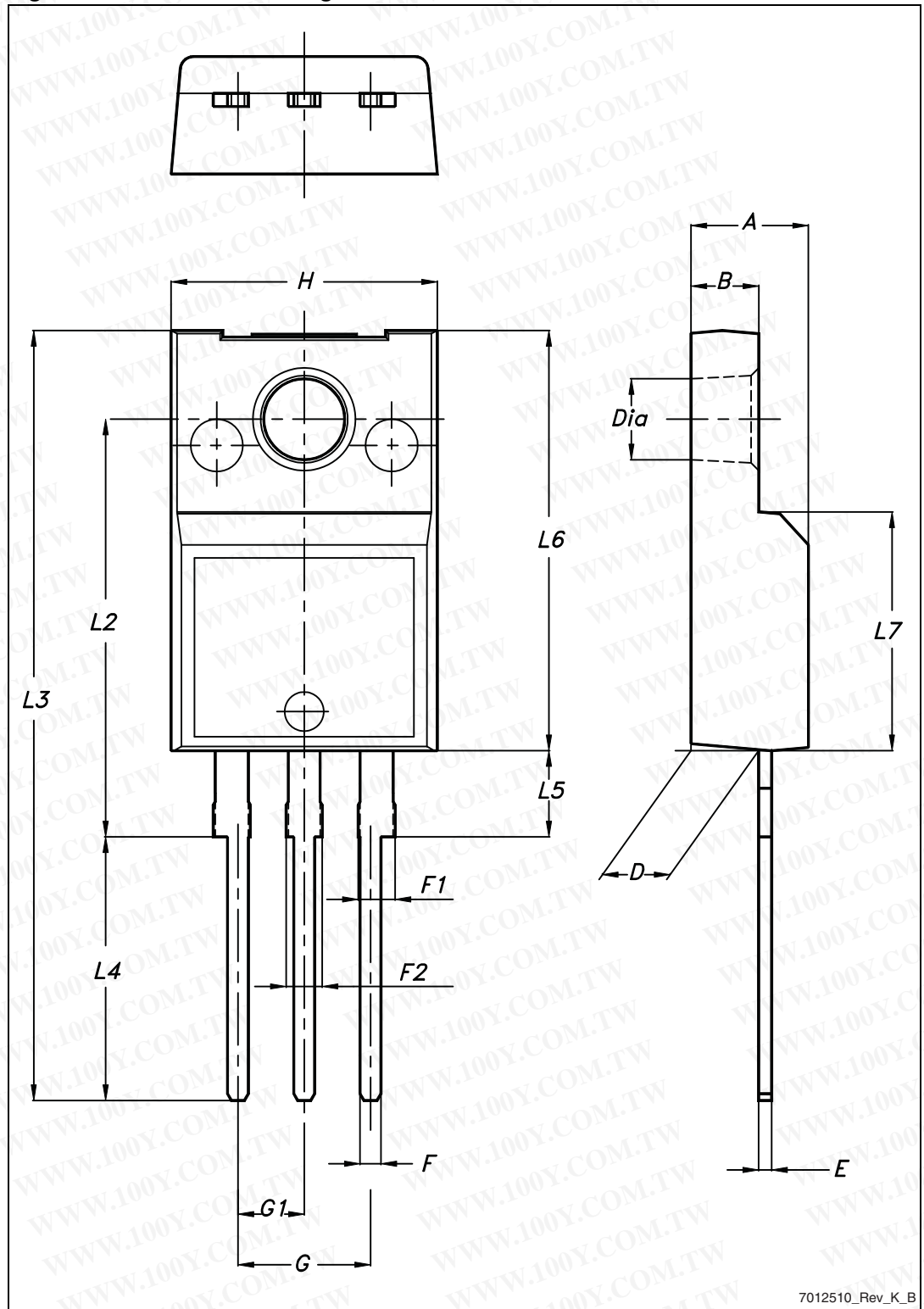




Table 10. I<sup>2</sup>PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 26. I<sup>2</sup>PAK (TO-262) drawing

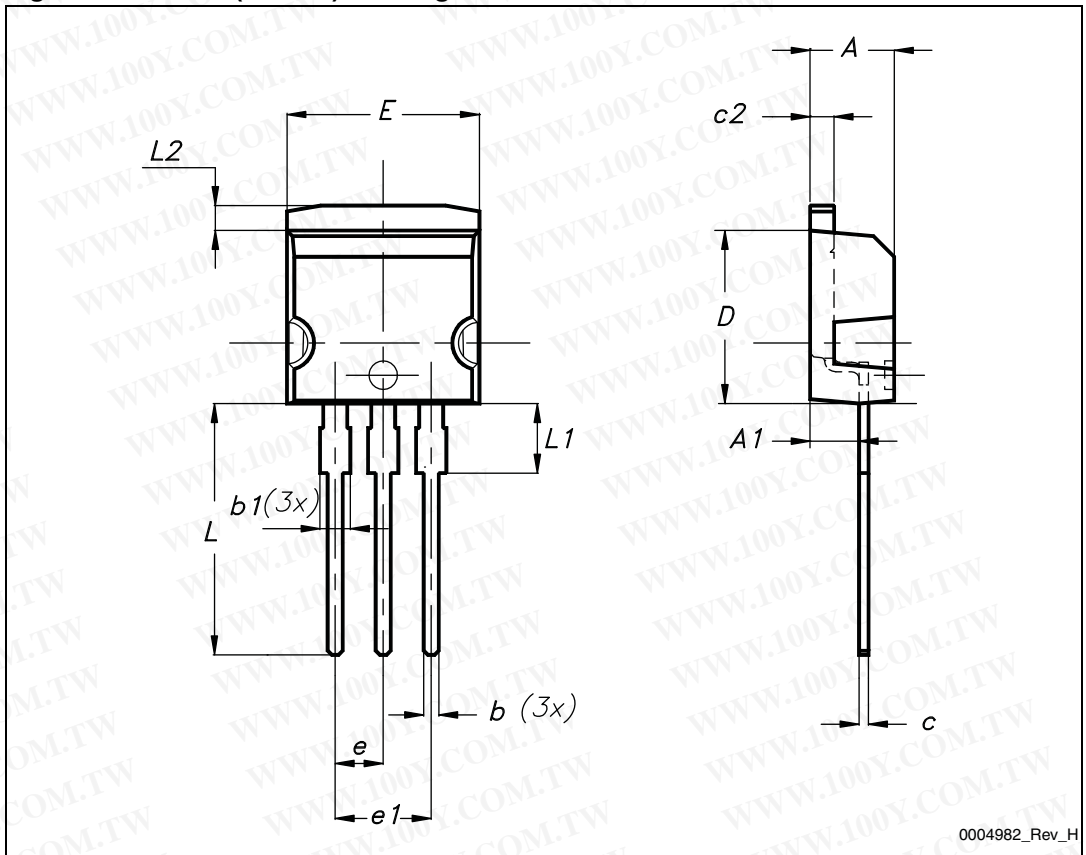
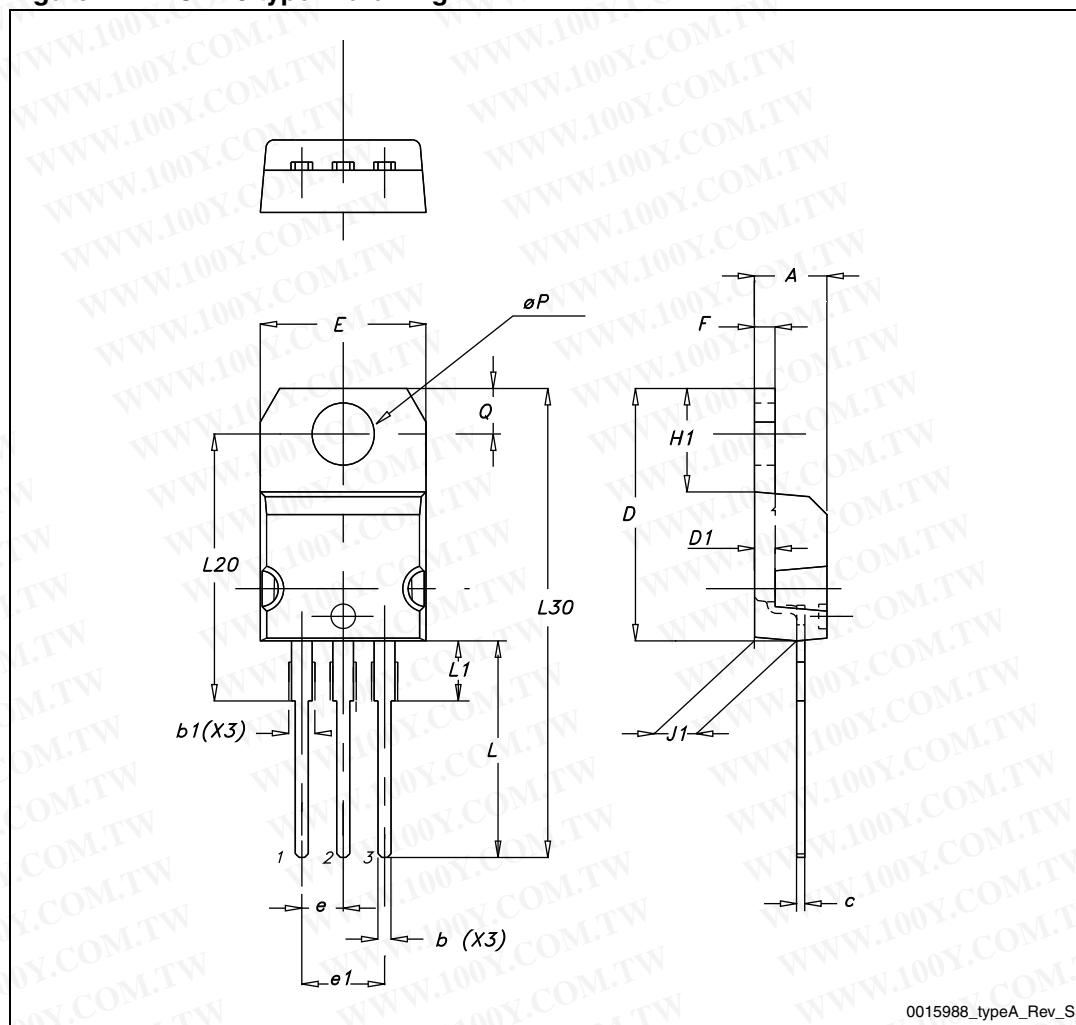


Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing



## 5 Packaging mechanical data

Table 12. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			



Figure 28. Tape

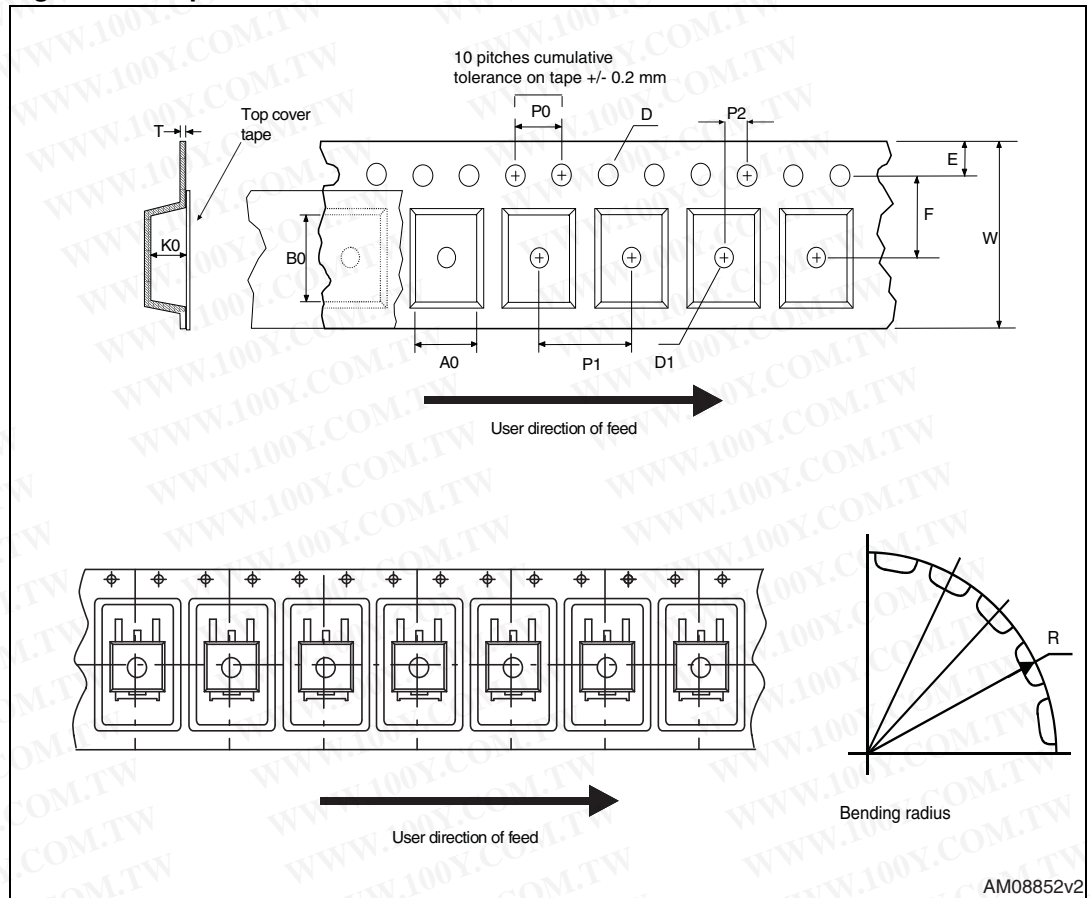
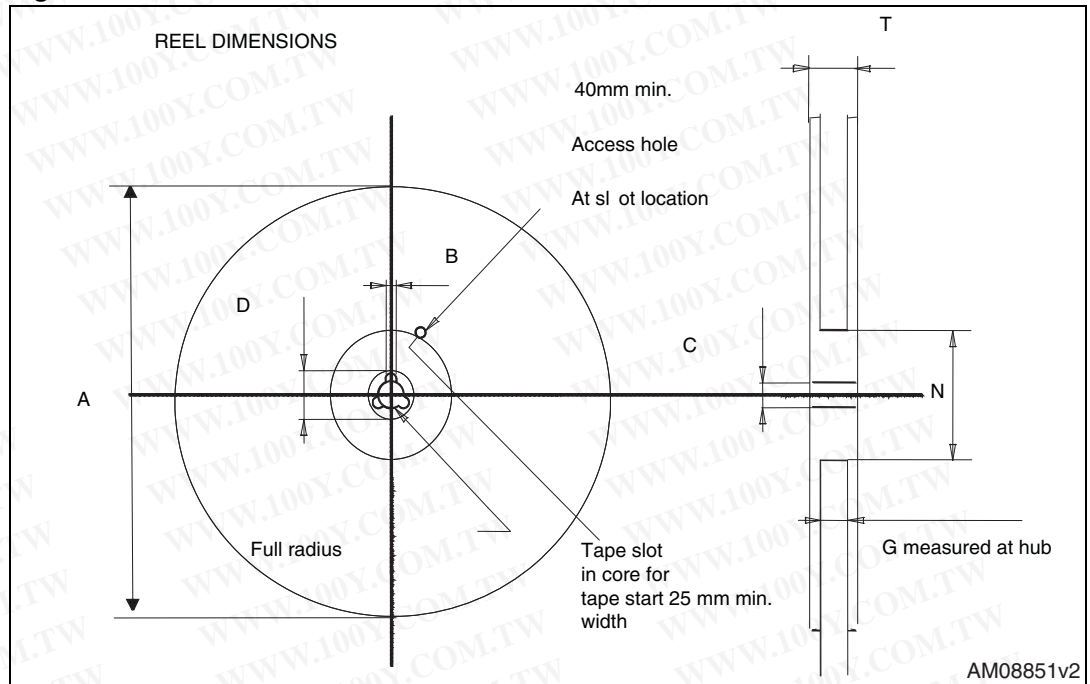


Figure 29. Reel



## 6 Revision history

**Table 13. Document revision history**

Date	Revision	Changes
06-Apr-2012	1	First release.
04-Jul-2012	2	Document status promoted from preliminary to production data. Added <a href="#">Section 2.1: Electrical characteristics (curves)</a> .
21-Aug-2012	3	Updated symbols and parameters in <a href="#">Table 6: Switching times</a> . Minor text change on the cover page.
04-Dec-2012	4	The part number STW57N65M5 has been moved to a separate datasheet.

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